

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. **(Currently Amended)** An alkaline cleaning solution comprising: an alkaline compound in an amount sufficient to render said solution alkaline, hydrogen peroxide in a concentration of 0.3 to 22% by weight, water and either 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] or 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and nitrilotriacetic acid as chelating additive(s), for removing and inhibiting metal contaminants from a semiconductor substrate surface in which metal impurity contamination becomes troublesome, and wherein said cleaning solution is free of phosphorus containing compounds.
2. **(Previously presented)** A cleaning solution according to claim 1, wherein the alkaline compound is an organic base, ammonia, ammonium hydroxide, or tetramethyl ammonium hydroxide.
3. **(Previously presented)** A cleaning solution according to claim 1, wherein the alkaline compound is ammonia or ammonium hydroxide.
4. **(Previously presented)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] in an amount in the range of 1000 to 3000 ppm.
5. **(Previously presented)** A cleaning solution according to claim 1, comprising nitrilotriacetic acid [NTA; CAS 139-13-9] in an amount in the range of 100 to 2000 ppm.
6. **(Previously presented)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and nitrilotriacetic acid in a total amount less than 4000 ppm.
7. **(Previously presented)** A cleaning solution according to claim 1, comprising 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and nitrilotriacetic acid in a total amount less than 2000 ppm.
8. **(Previously presented)** A method for cleaning a semiconductor substrate comprising treating the semiconductor substrate with a cleaning solution according to claim 1, and drying said semiconductor substrate after water rinsing.

9. **(Previously presented)** A method of treatment according to claim 8, wherein the treatment with cleaning solution is carried out at a temperature the range of 20 to 80 °C.
10. **(Previously presented)** A method of treatment according to claim 8, wherein the treatment with cleaning solution is carried out at normal room temperature.
11. **(Previously presented)** A method of treatment according to claim 8, wherein said cleaning solution is brought into contact with a surface to be cleaned for a few seconds to 60 minutes.
12. **(Previously presented)** A method of treatment according to claim 8, wherein said cleaning solution is brought into contact with a surface to be cleaned for about 15 seconds to 15 minutes.
13. **(Previously presented)** A method for treatment of a semiconductor substrate according to claim 8, wherein the semi-conductor substrate is immersed / dipped in the cleaning solution.
14. **(Previously presented)** A method for surface treatment operations including cleaning, etching, polishing, film-forming, for the cleaning of substrates such as semiconductor, metal, glass, ceramics, plastic, magnetic material, superconductors comprising contacting said surface with a cleaning solution according to claim 1.
15. **(Withdrawn-currently amended)** A combination comprising:
- a) a semiconductor substrate having a surface and
 - b) an alkaline cleaning solution comprising an alkaline compound, hydrogen peroxide in a concentration of 0.3 to 22% by weight , water
- and
- 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] or
- 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris]
and nitrilotriacetic acid as chelating additive(s),

wherein said cleaning solution is capable of removing and inhibiting metal contamination on the surface of said semiconductor substrate, and wherein said cleaning solution is free of phosphorus containing compounds .